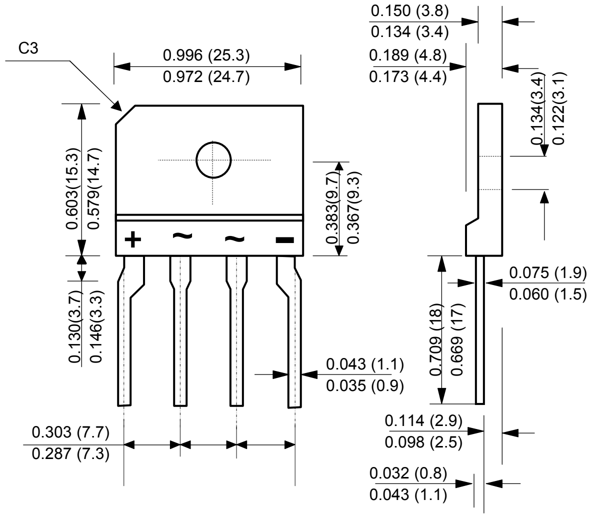
TH97/10561QM TW00/17276EM IATF 0060636
SGS TH07/1033

D10XB60H

SILICON BRIDGE RECTIFIER

RBV4



Dimensions in inches and (millimeters)

PRV : 600 Volts
Io : 10 Amperes

FEATURES :

- Glass passivated junction chip
- High current capability
- High surge current capability
- High reliability
- Low reverse current
- Low forward voltage drop
- Ideal for printed circuit board
- Very good heat dissipation
- Pb / RoHS Free

MECHANICAL DATA :

- Case : Reliable low cost construction
  utilizing molded plastic technique
- Epoxy : UL94V-O rate flame retardant
- Terminals : Plated lead solderable per
  MIL-STD-202, Method 208 guaranteed
- Polarity : Polarity symbols marked on case
- Mounting position : Any
- Weight : 4.28 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

RATING		SYMBOL	VALUE	UNIT
Maximum Peak Reverse Voltage		V_{RM}	600	V
Maximum Average Forward Current (50Hz Sine wave, R-load)	With heatsink, Tc = 112 °C Without heatsink, Ta = 25 °C	I_O	10 2.9	A
Maximum Peak Forward Surge Current, Tj = 25 °C (50Hz sine wave, Non-repetitive 1 cycle peak value)		I_{FSM}	170	A
Current Squared Time at 1ms ≤ t < 10 ms, T_J = 25 °C		I^2t	110	A^2S
Maximum Forward Voltage per Diode at IF = 5.0 A (Pulse measurement, Rating of per diode)		V_F	1.05	V
Maximum DC Reverse Current, V_R=V_{RM} (Pulse measurement, Rating of per diode)		I_R	10	µA
Maximum Thermal Resistance, Junction to case, With heatsink		$R_{\theta JC}$	1.9	°C/W
Maximum Thermal Resistance, Junction to Ambient, Without heatsink		$R_{\theta JA}$	26	°C/W
Maximum Thermal Resistance, Junction to Lead, Without heatsink		$R_{\theta JL}$	6	°C/W
Operating Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{STG}	- 40 to + 150	°C

RATING AND CHARACTERISTIC CURVES (D10XB60H)

FIG.1 - DERATING CURVE

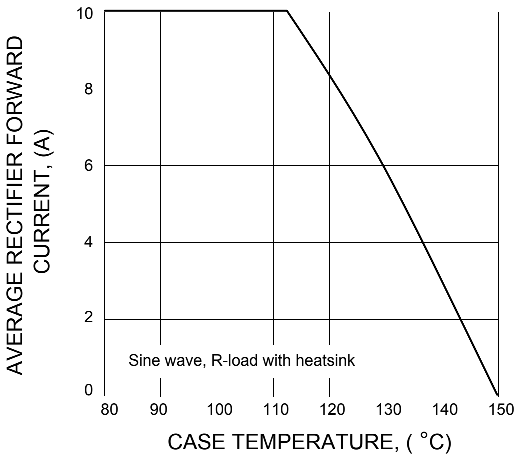


FIG.2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

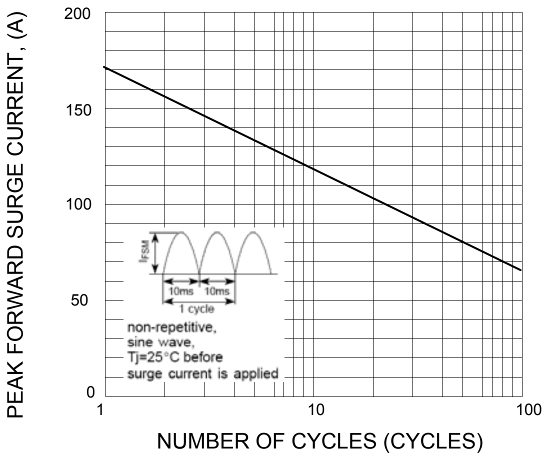


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

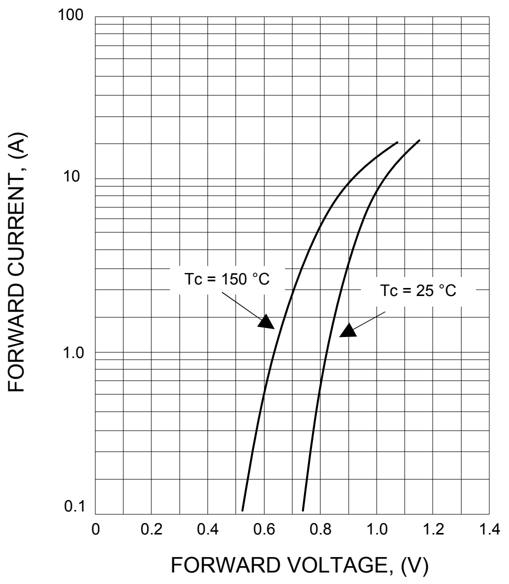


FIG.4 - POWER DISSIPATION